



FEATURES

- Ideal for electron detection
- Large detection area
- 100% internal QE

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	10mm x 10mm		100		mm ²
Responsivity, \mathcal{R}	(see graphs on next page)				A/W
Shunt Resistance, R _{sh}	V _B = ±10mV	10	50		M-ohm
Reverse Breakdown Voltage, V _R	I _R = 1μA	5	10		Volts
Capacitance, C	V _R = 0V		10	44	nF
Rise Time	V _R = 0V, R _L = 50Ω		10		usec

THERMAL PARAMETERS

Storage and Operating Temperature Range	-40°C TO 70°C
Maximum Junction Temperature	70°C
Lead Soldering Temperature ¹	260°C

¹0.08" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond. Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.

